Supertex inc.

16-Channel Serial to Parallel Converter with High Voltage Backplane Driver and Push-Pull Outputs

Features

- ► HVCMOS[®] technology
- Output voltage up to +200V
- Shift register speed 500kHz @ V_{DD} = 2.0V
- 16 high voltage outputs
- High voltage backplane driver
- CMOS input levels

Applications

- Multiple segment EL display
- Piezoelectric transducer driver
- Braille driver

General Description

The HV509 is a 200V, 16-channel serial to parallel converter. The high voltage outputs and the backplane driver are designed to source and sink \pm 1.0mA.

The high voltage outputs are controlled by a 16-bit serial shift register, followed by a 16-bit latch. Data is shifted through the shift registers during the low to high clock transition. A data output buffer is provided for cascading multiple devices. Data is transferred to the 16-bit latch when a logic level low is applied to the LE input. Data is stored in the latch when $\overline{\text{LE}}$ is high. Output states are controlled by the data in the latch and by the POL pin.



Typical Application Circuit

Ordering Information

| Device | Package Option | | | | | | |
|--------|---------------------|--|--|--|--|--|--|
| | 32-Lead QFN | | | | | | |
| | 5.00x5.00mm body | | | | | | |
| | 1.00mm height (max) | | | | | | |
| | 0.50mm pitch | | | | | | |
| HV509 | HV509K6-G | | | | | | |
| | 4 | | | | | | |

-G indicates package is RoHS compliant ('Green')



Absolute Maximum Ratings

| Parameter | Value |
|---|---------------------------------|
| Logic supply, $V_{_{DD}}$ | -0.5V to 7.0V |
| High voltage supply, $V_{_{PP}}$ | 215V |
| Translator supply voltage, $V_{\rm BIAS}$ | -0.5V to 7.0V |
| Logic input levels | -0.5V to V _{DD} + 0.5V |
| Operating junction temperature | -40°C to +125°C |
| Storage temperature range | -65°C to +150°C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



Pads are at the bottom of the package. Exposed heat slug is at V_{PP} potential.

Product Marking



Operating Supply Voltages and Conditions

| Sym | Parameter | Min | Тур | Max | Units | Conditions |
|-------------------|---------------------------------|--------------------|-----|--------------------|-------|------------|
| V _{DD} | Logic supply voltage | 2.0 | 3.0 | 5.5 | V | |
| V _{BIAS} | Level translator supply voltage | 2.6 | - | 6.6 | V | |
| V _{PP} | Positive high voltage supply | 50 | - | 200 | V | |
| V _{IH} | High-level input voltage | 0.9V _{DD} | - | V _{DD} | V | |
| V _{IL} | Low-level input voltage | 0 | - | 0.1V _{DD} | V | |
| T _A | Operating temperature | 0 | - | +70 | °C | |

Notes:

1. External ground noise reduction circuit will be provided by design upon characterization.

- 2. Power-up sequence should be the following*:
 - 1. Apply ground
 - 2. Apply V_{DD}
 - 3. Set all inputs (D_{IN}, CLK, LE, POL) to a known state
 - 4. Apply V_{BIAS}
 - 5. Apply V_{PP}
- 3. Power-down sequence should be the reverse of the above.

*This power up sequence requires an external high voltage diode between VDD and VPP. Without the diode, power up VPP to a VDD level first to bias the silicon substrate. After all other signals are powered, finish raising the V_{pp} to its final level.

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| | iectrical charat | | Over operating su | ppiy voitag | jes and tem | uniess otherwise noted) | |
|--------------------|-----------------------------------|------------------------|------------------------|-------------|-------------|--|--|
| Sym | Parameter | Min | Тур | Max | Units | Conditions | |
| I _{DD} | V _{DD} supply current | | - | - | 1.0 | mA | f _{clk} = 500kHz |
| I _{DDQ} | Quiescent V _{DD} supply | v current | - | - | 10 | μA | All logic inputs = V _{DD} or 0V |
| I _{BIAS} | V _{BIAS} supply current | - | - | 100 | μA | All HV _{OUTS} switching at 1kHz. Peak I _{BIAS} = 200mA with all channels switching | |
| I _{BIASQ} | Quiescent V _{BIAS} curre | nt | - | - | 10 | μA | No HV _{out} switching |
| I _{PPQ} | Quiescent V _{PP} supply | - | - | 100 | μA | $V_{_{PP}}$ = 200V, outputs are static | |
| I _{IH} | High-level logic input | - | - | 10 | μA | V _{IH} = V _{DD} | |
| I | Low-level logic input | current | - | - | -10 | μA | V _{IL} = 0V |
| | | | V _{PP} - 12V | - | - | V | IHV _{OUT} = -1.0mA, V _{PP} = +200V |
| V _{OH} | High level output | HV _{OUT} & BP | V _{PP} - 12V | | - | V | IHV _{OUT} = -1.0mA, V _{PP} = +50V |
| | | D _{OUT} | V _{DD} - 1.0V | - | - | V | ID _{out} = -1.0mA |
| V _{ol} | Low level output | HV _{OUT} & BP | - | - | 12 | V | $IHV_{OUT} = 1.0mA, V_{BIAS} = 5.4V, V_{PP} = +50 \text{ to } +200V$ |
| | | D _{OUT} | - | - | 1.0 | V | ID _{out} = 1.0mA |
| C _{DIN} | Logic input capacitan | - | - | 10 | pF | | |
| C _{DOUT} | Logic output capacita | ince | - | - | 10 | pF | |

DC Electrical Characteristics (Over operating supply voltages and temperature, unless otherwise noted)

AC Electrical Characteristics (Over operating supply voltages and temperature, unless otherwise noted)

| Sym | Parameter | Min | Тур | Мах | Units | Conditions |
|------------------|--|--------------------------------------|-----|-----|-------|---|
| f _{CLK} | Clock frequency | 0 | - | 500 | kHz | |
| t _c | Clock high / low pulse width | 1.0 | - | - | μs | |
| t _{su} | Data setup time before clock rises | 50 | - | - | ns | |
| t _H | Data hold time after clock rises | 50 | - | - | ns | |
| t _{cle} | LE from CLK setup time | 15 | - | - | ns | |
| t _{wLE} | LE pulse width | 100 | - | - | ns | |
| t _{DD} | Clock negative edge to D_{OUT} delay | - | - | 150 | ns | $C_{LDOUT} = 50 pF,$ (C_{LDOUT} includes C_{DIN} and C_{DOUT}) |
| t _{PHV} | Delay time from inputs for HV _{out} / BP to start rise/fall | - | - | 500 | ns | V _{PP} = 200V, V _{BIAS} = 5.4V |
| t _{or} | HV _{OUTPUT} / BP rise time | - | - | 300 | μs | C _L = 1500pF, V _{PP} = 200V |
| t _{oF} | HV _{output} / BP fall time | - | - | 300 | μs | C_{L} = 1500pF, V_{BIAS} = 5.4V, V_{PP} = 200V |
| t _{oc} | Width of POL pulses | $t_{_{PHV}}$ + $t_{_{OR}}/t_{_{OF}}$ | - | - | μs | |

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Input and Output Equivalent Circuits



V_{BIAS} SUPPLY

The V_{BIAS} supply operates from 2.6V to 6.6V. It is the gate drive voltage for all of the output N-channel MOSFETs. This allows the output peak current sink to be set by varying the V_{BIAS} voltage. A higher V_{BIAS} voltage will increase the current sinking capability.

If large peak currents are not required, V_{DD} and V_{BIAS} can be connected to the same power supply, provided they are both within the operating range. The operating V_{DD} range is 2.0V to 5.5V. A plot showing the typical characteristics of I_{SINK} vs V_{BIAS} is shown below.



Typical HV_{OUT} I_{SINK} vs V_{BIAS} (V_{PP} = 200V, C_{IOAD} = 1nF)

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Switching Waveforms



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Functional Block Diagram



Function Table

| | | Inp | uts | | Outputs | | | | | | |
|-----------------------|-----------------|----------|-----|-----|--------------------|-------------|---|------------------|--|--|--|
| Function | D _{IN} | CLK | LE | POL | Shift Reg 1 216 | | | D _{out} | | | |
| Load S/R | H OR L | ↑ | Н | Х | HorL ●● | • •• | Х | • | | | |
| Transfer data in | Х | L | L | Н | * ** | * ** | L | • | | | |
| latch | Х | L | L | L | * ** | * ** (b) | Н | • | | | |
| | Х | Х | Н | Н | • •• | • •• | L | • | | | |
| Store data in latches | Х | Х | Н | L | • •• | • •• (b) | Н | • | | | |
| Transporent mode | L | Ť | L | Н | L ●● | L ●● | L | • | | | |
| Transparent mode | Н | Ť | L | Н | Η ●● | Η ●● | L | • | | | |
| Invert mode | Х | Х | Н | L | • •• | • •• (b) | Н | x | | | |
| | Х | Х | Н | Н | • •• | • •• | L | X | | | |

Notes:

H = high level, L = low level, X = irrelevant, ↑ = low-to-high transition_

• = dependent on previous stage's state before the last CLK or last $\overline{\text{LE}}$ low

* = data at the last CLK \uparrow

(b) = bar over all symbols

Pin Description

| Pin # | Function | Description |
|-------|----------------------|-------------------------------|
| 1 | HV _{out} 12 | High voltage push-pull output |
| 2 | HV _{out} 11 | High voltage push-pull output |
| 3 | HV _{out} 10 | High voltage push-pull output |
| 4 | HV _{out} 9 | High voltage push-pull output |
| 5 | HV _{out} 8 | High voltage push-pull output |
| 6 | HV _{out} 7 | High voltage push-pull output |
| 7 | HV _{out} 6 | High voltage push-pull output |
| 8 | HV _{out} 5 | High voltage push-pull output |
| 9 | HV _{out} 4 | High voltage push-pull output |
| 10 | HV _{out} 3 | High voltage push-pull output |
| 11 | HV _{out} 2 | High voltage push-pull output |
| 12 | HV _{out} 1 | High voltage push-pull output |
| 13 | NC | No connect |
| 14 | VPP | High voltage supply |
| 15 | GND | Logic ground |
| 16 | NC | No connect |
| 17 | DIN | Data in |
| 18 | NC | No connect |
| 19 | CLK | Clock input logic |
| 20 | VDD | Logic supply voltage |
| 21 | POL | Polarity bar input logic |
| 22 | Ē | Latch enable bar input logic |
| 23 | NC | No connect |
| 24 | DOUT | Data out |
| 25 | NC | No connect |
| 26 | VBIAS | Level translator bias voltage |
| 27 | HVGND | High voltage ground |
| 28 | BP | High voltage backplane output |
| 29 | HV _{out} 16 | High voltage push-pull output |
| 30 | HV _{out} 15 | High voltage push-pull output |
| 31 | HV _{out} 14 | High voltage push-pull output |
| 32 | HV _{out} 13 | High voltage push-pull output |

32-Lead QFN Package Outline (K6) 5.00x5.00mm body, 1.00mm height (max), 0.50mm pitch



Notes:

- 1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 Identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.
- 2. Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

| Symb | ol | Α | A1 | A3 | b | D | D2 | E | E2 | е | L | L1 | θ |
|-------------------|-----|------|------|-------------|------|-------|-------------------|-------|-------------------|-------------|-------------------|------|-----------------|
| | MIN | 0.80 | 0.00 | | 0.18 | 4.85* | 1.05 | 4.85* | 1.05 | | 0.30† | 0.00 | 0 0 |
| Dimension (mm) | NOM | 0.90 | 0.02 | 0.20 REF | 0.25 | 5.00 | - | 5.00 | - | 0.50 BSC | 0.40 [†] | - | - |
| (mm) | MAX | 1.00 | 0.05 | | 0.30 | 5.15* | 3.55 [†] | 5.15* | 3.55 [†] | DOO | 0.50 [†] | 0.15 | 14 ⁰ |

JEDEC Registration MO-220, Variation VHHD-6, Issue K, June 2006.

* This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

† This dimension is a non-JEDEC dimension.

Drawings not to scale.

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(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>http://www.</u> supertex.com/packaging.html.)

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